

## **APPENDIX B**

### **Claims of U.S. Patent No. 6,225,034 to Tanabe *et al.***

1. In a method of stripping photoresists comprising the following steps:

- (I) forming a photoresist layer on a substrate having metallic layer(s) thereon;
- (II) selectively exposing the applied photoresist layer to light through a mask pattern;
- (III) developing the light-exposed photoresist layer to provide a photoresist pattern;
- (IV) etching the substrate through the photoresist pattern as a mask pattern; and
- (V) stripping away the photoresist pattern from the substrate;

the improvement wherein the photoresist pattern is stripped with a photoresist stripping liquid composition comprising (a) 2-30 wt. % of a hydroxylamine, (b) 2-35 wt. % of water, (c) 25-40 wt. % of at least one member selected from monoethanolamine and diethanolamine, (d) 20-32 wt. % of dimethyl sulfoxide and (e) 2-20 wt. % of an aromatic hydroxy compound, at a temperature of 75-85° C.

2. The method of stripping photoresists according to claim 1, wherein said metallic layer(s) formed on the substrate involve at least a pure titanium (Ti) layer.

3. The method according to claim 1 wherein the metallic layer(s) contain(s) Al or Al alloy.

4. The method according to claim 1 wherein the metallic layer(s) contain(s) Ti.

5. In a method of stripping photoresists consisting of the following steps:

- (I) forming a photoresist layer on a substrate having metallic layer(s) thereon;
- (II) selectively exposing the applied photoresist layer to light through a mask pattern;
- (III) developing the light-exposed photoresist layer to provide a photoresist pattern;
- (IV) etching the substrate through the photoresist pattern as a mask pattern;

(V) ashing the photoresist pattern; and

(VI) stripping away the thus ashed photoresist pattern from the substrate;

the improvement wherein the ashed photoresist pattern is stripped with the photoresist stripping liquid composition comprising (a) 2-30 wt. % of a hydroxylamine, (b) 2-35 wt. % of water, (c) 25-40 wt. % of at least one member selected from monoethanolamine and diethanolamine, (d) 20-32 wt. % of dimethyl sulfoxide and (e) 2-20 wt. % of an aromatic hydroxy compound, at a temperature of 75-85.degree. C.

6. The method of stripping photoresists according to claim 5, wherein said metallic layer(s) formed on the substrate involve at least a pure titanium (Ti) layer.

7. The method according to claim 5 wherein the metallic layer(s) contain(s) Al or Al alloy.

8. The method according to claim 5 wherein the metallic layer(s) contain(s) Ti.